

SWITCHING REGULATOR APPLICATIONS

Features

- High Voltage : $BV_{DSS}=500V(\text{Min.})$
- Low C_{RSS} : $C_{RSS}=6.5pF(\text{Typ.})$
- Low gate charge : $Q_g=8.5nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=3.3\Omega(\text{Max.})$

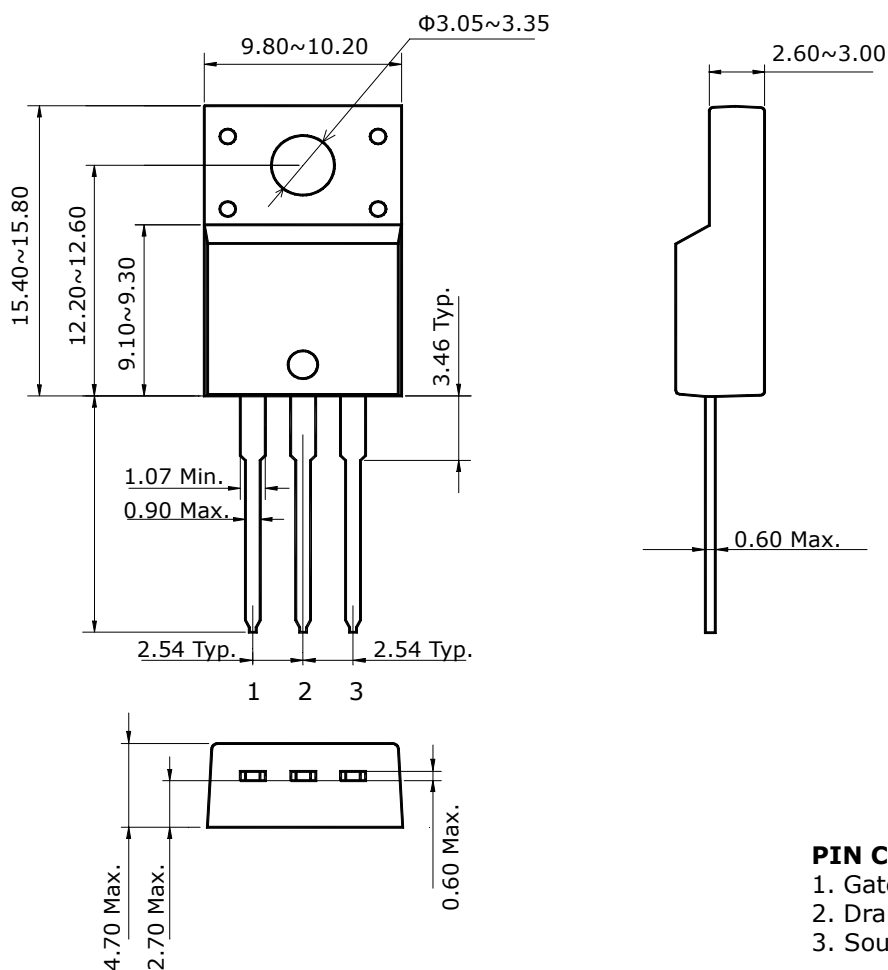
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Ordering Information

Type NO.	Marking	Package Code
STK0250F	STK0250	TO-220F-3L

Outline Dimensions

unit : mm



PIN Connections

1. Gate
2. Drain
3. Source

Absolute maximum ratings

(Tc=25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	500	V
Gate-source voltage	V_{GSS}	±30	V
Drain current (DC)	I_D	(Tc=25°C)	A
		(Tc=100°C)	A
Drain current (Pulsed) *	I_{DP}	8.0	A
Drain Power dissipation	P_D	22	W
Avalanche current (Single) ②	I_{AS}	2.0	A
Single pulsed avalanche energy ②	E_{AS}	59	mJ
Avalanche current (Repetitive) ①	I_{AR}	2.0	A
Repetitive avalanche energy ①	E_{AR}	3.0	mJ
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55~150	

* Limited by maximum junction temperature

Characteristic		Symbol	Typ.	Max	Unit
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	5.7	°C/W
	Junction-ambient	$R_{th(J-a)}$	-	62.5	

Electrical Characteristics

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0$	500	-	-	V
Gate-threshold voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	3.0	-	5.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$	-	-	1	μA
Gate-source leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 30V$	-	-	± 100	nA
Drain-Source on-resistance ④	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1.0A$	-	3.1	3.4	Ω
Forward transfer admittance ④	g_{fs}	$V_{DS}=10V, I_D=1.0A$	-	1.4	-	S
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V, f=1MHz$	-	268	402	pF
Output capacitance	C_{oss}		-	13	19.5	
Reverse transfer capacitance	C_{rss}		-	6.5	9.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=250V, V_{GS}=10V$ $I_D=2.0A, R_G=25\Omega$ ③④	-	8.5	-	ns
Rise time	t_r		-	10.2	-	
Turn-off delay time	$t_{d(off)}$		-	19	-	
Fall time	t_f		-	10.2	-	
Total gate charge	Q_g	$V_{DD}=250V, V_{GS}=10V$ $I_D=2.0A$ ③④	-	8.5	12.8	nC
Gate-source charge	Q_{gs}		-	1.7	2.6	
Gate-drain charge	Q_{gd}		-	3.0	4.5	

Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous source current	I_S	Integral reverse diode in the MOSFET	-	-	2	A
Source current (Pulsed) ①	I_{SP}		-	-	8	
Forward voltage ④	V_{SD}	$V_{GS}=0V, I_S=2.0A$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_S=2.0A, V_{GS}=0V$ $di_s/dt=100A/\mu s$	-	200	-	ns
Reverse recovery charge	Q_{rr}		-	0.7	-	μC

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=26.5mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$
- ③ Pulse Test : Pulse Width < 300 μs , Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

STK0250F

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Fig. 1 $I_D - V_{DS}$

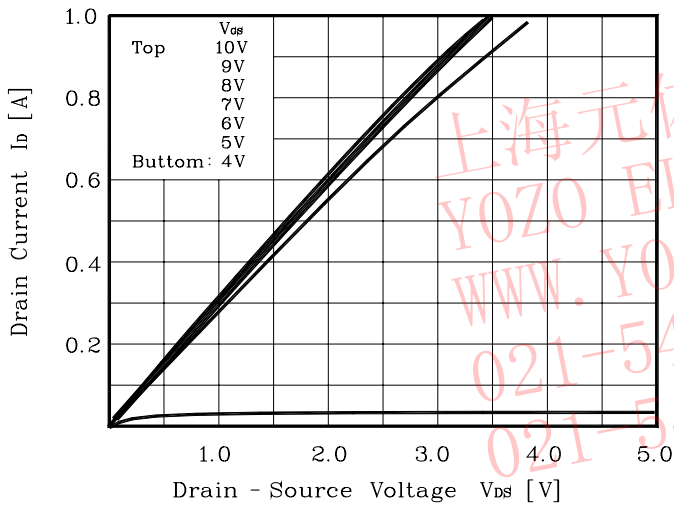


Fig. 2 $I_D - V_{GS}$

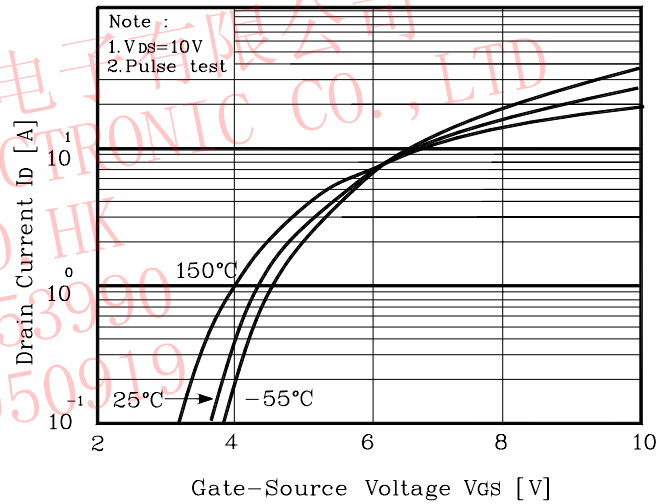


Fig. 3 $R_{DS(on)} - I_D$

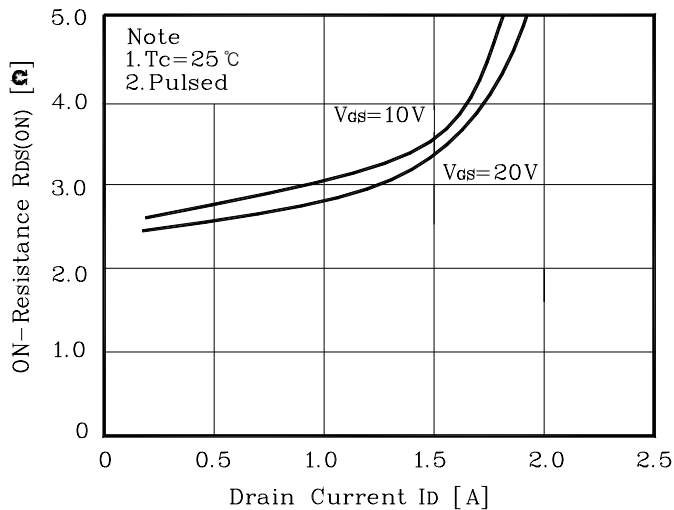


Fig. 4 $I_S - V_{SD}$

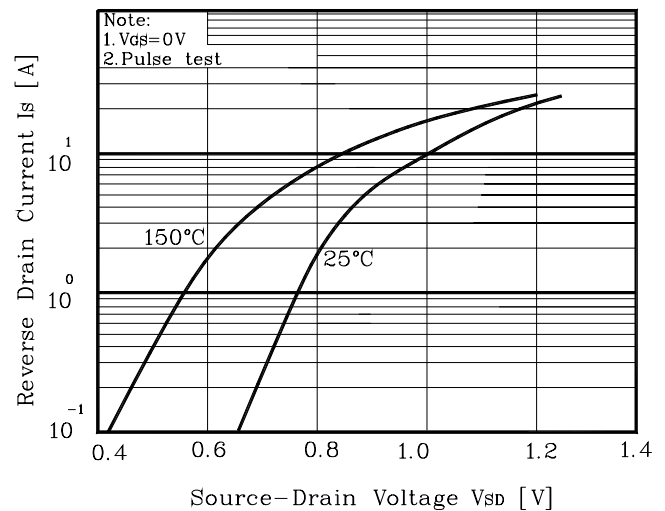


Fig. 5 Capacitance - V_{DS}

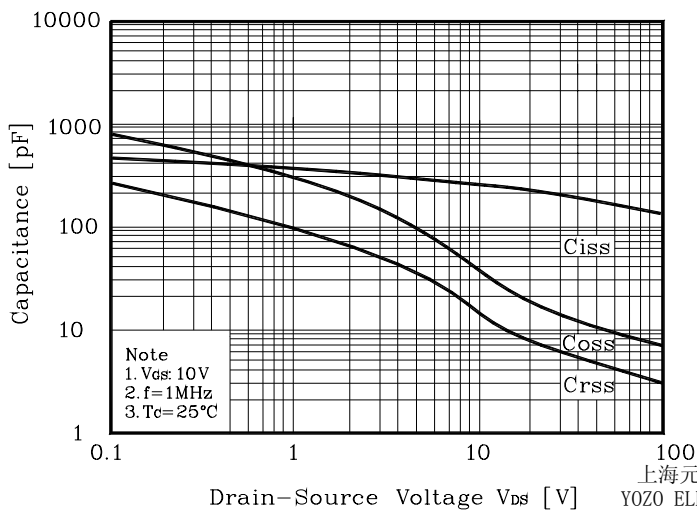


Fig. 6 $V_{GS} - Q_G$

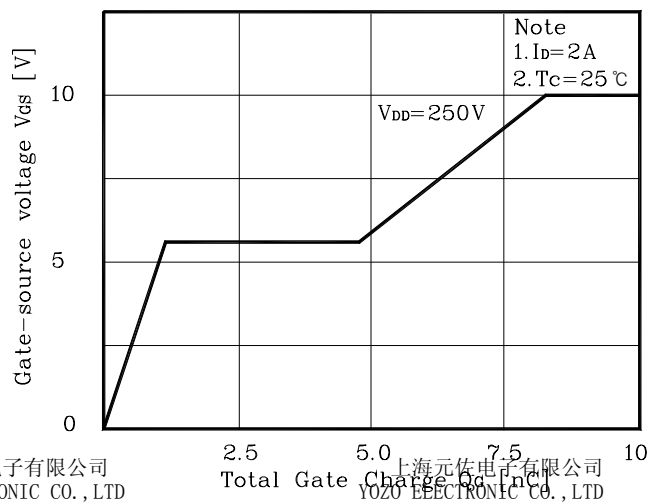


Fig. 7 $V_{DS} - T_J$

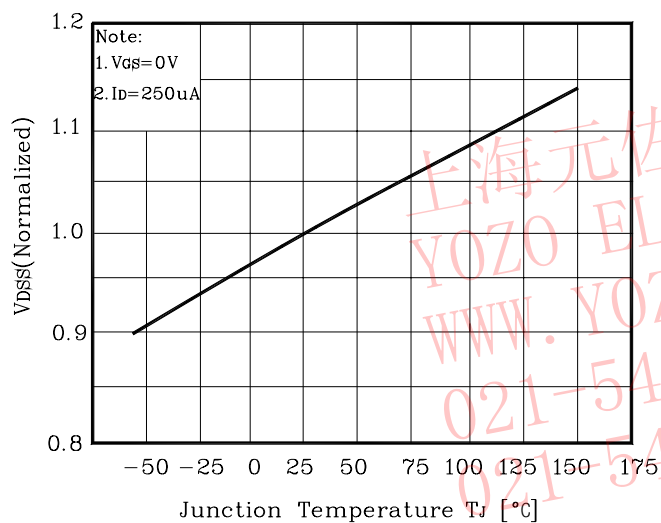
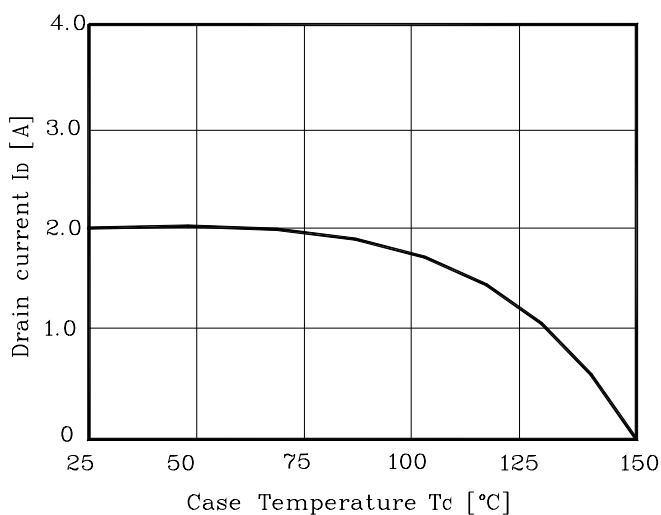


Fig. 9 $I_D - T_C$



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Fig. 8 $R_{DS(on)} - T_J$

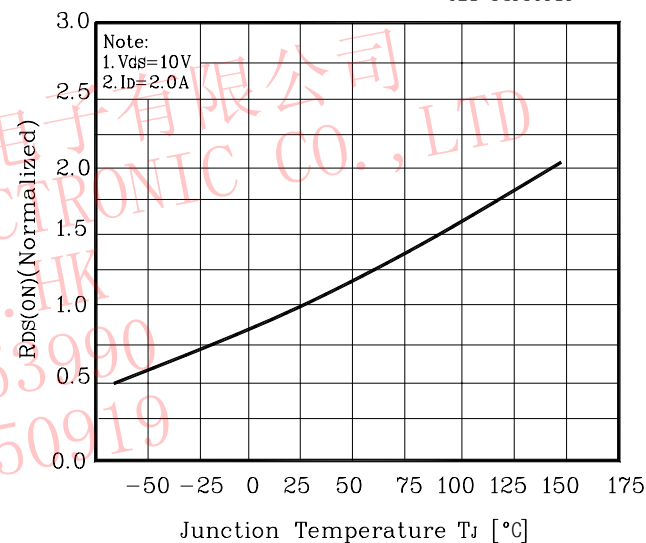


Fig. 10 Safe Operating Area

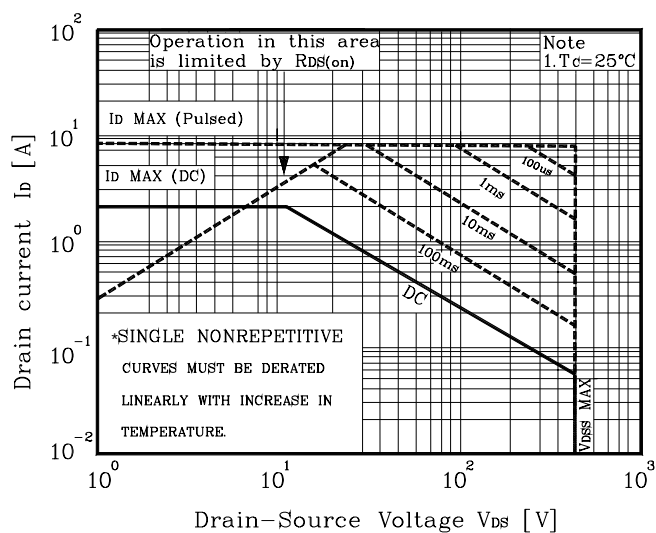


Fig. 11 Gate Charge Test Circuit & Waveform

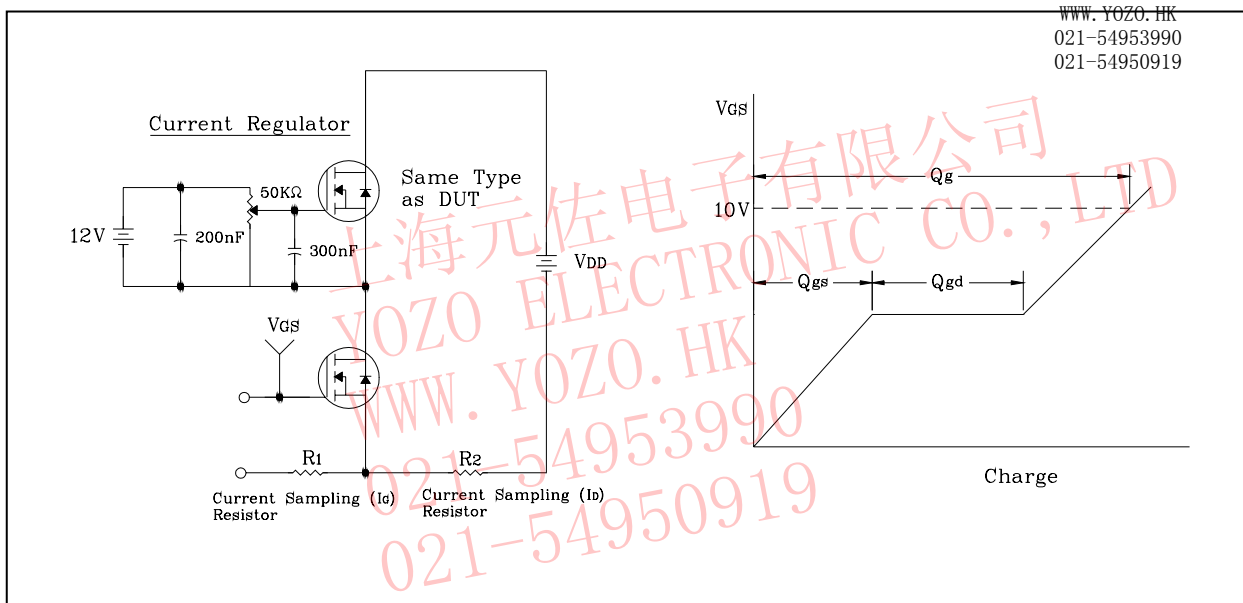


Fig. 12 Resistive Switching Test Circuit & Waveform

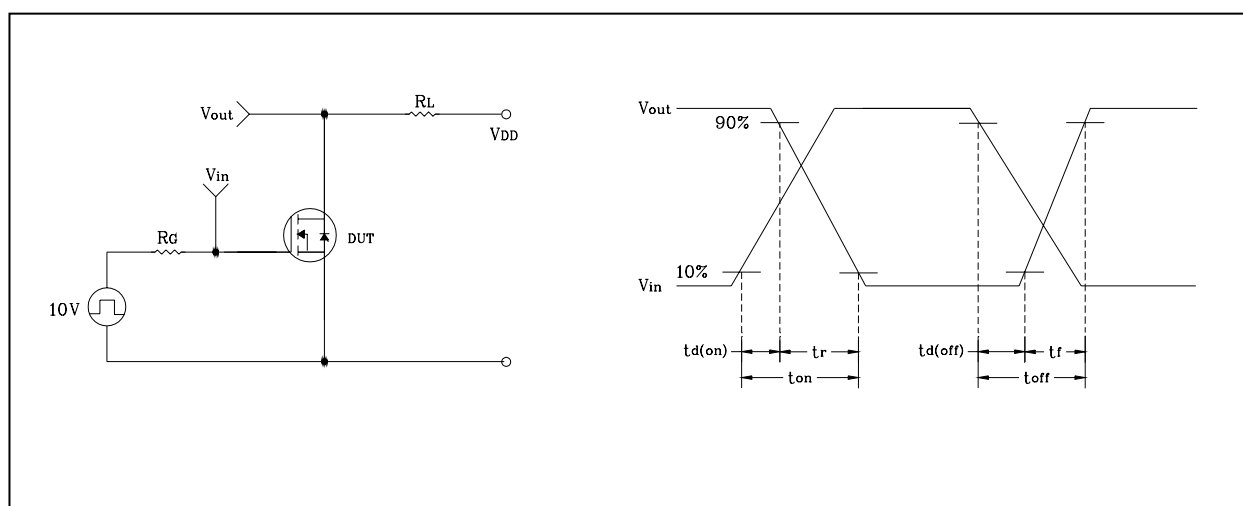


Fig. 13 EAS Test Circuit & Waveform

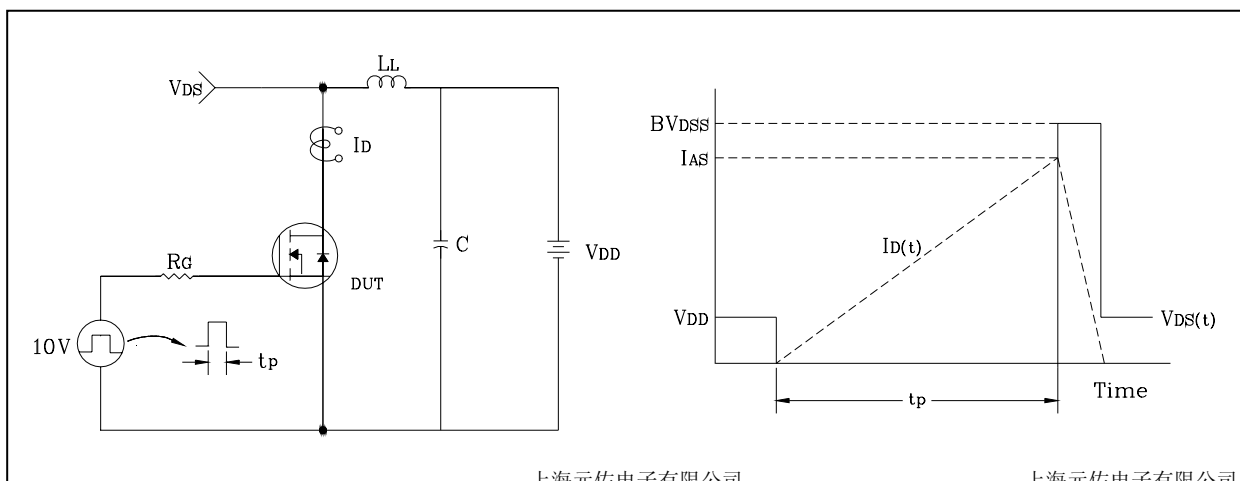


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform

